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60V DUAL N-CHANNEL 175°C MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
60V	27mΩ @ V _{GS} = 10V	22.6A
	30mΩ @ V _{GS} = 6V	21.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

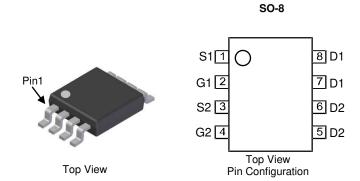
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

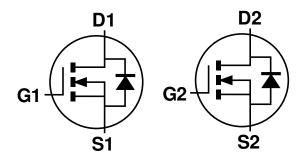
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g Minimiszs Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.074 grams (Approximate)





Equivalent Circuit

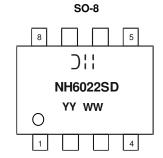
Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6022SSD-13	SO-8	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦ = Manufacturer's Marking NH6022SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)

August 2016



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Dusin Comment V 40V (Note C)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	22.6 16.0	Α
Continuous Drain Current V _{GS} = 10V (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.1 5.9	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	45	Α
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2	Α	
Avalanche Current L=0.1mL (Note 7)		I _{AS}	22	Α
Avalanche Energy L=0.1mL (Note 7)		E _{AS}	24	mJ

Thermal Characteristics

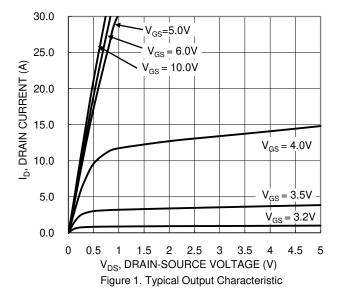
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	104	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	60	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	74	°C/W
Thermal nesistance, bunction to Ambient (Note o)	t<10s	$R_{ heta JA}$	42	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	7.25	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	٧	$V_{DS}=V_{GS},\ I_D=250\mu A$	
Static Drain-Source On-Resistance	В		21	27	mΩ	$V_{GS} = 10V, I_D = 5A$	
Static Diain-Source On-nesistance	R _{DS(ON)}	_	24	30	11122	$V_{GS} = 6V$, $I_D = 5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	1	2127		pF	V 05V V 0V	
Output Capacitance	Coss	1	86	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	54	_	pF	1 = 1.0WHZ	
Gate Resistance	R_g	_	2.0	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at (V _{GS} = 10V)	Q_g	_	32	_	nC		
Total Gate Charge at (V _{GS} = 4.5V)	Q_{g}	-	14	_	nC	\/ 20\/ I- 6A	
Gate-Source Charge	Q _{gs}	_	7	_	nC	$V_{DS} = 30V$, $I_D = 6A$	
Gate-Drain Charge	Q_{gd}	_	4	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.4	_	ns		
Turn-On Rise Time	t _R	_	4.4	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	30.4	_	ns	$R_g = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _F	_	8.4	_	ns]	
Body Diode Reverse Recovery Time	t _{RR}	_	18.1	_	ns	$I_F = 1.7A$, $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge	Q _{RR}	_	12.5	_	nC	$I_F = 1.7A$, $di/dt = 100A/\mu s$	

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
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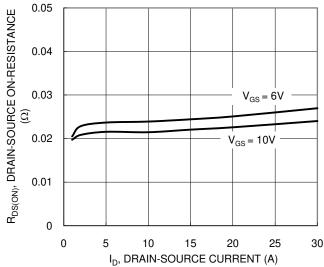


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

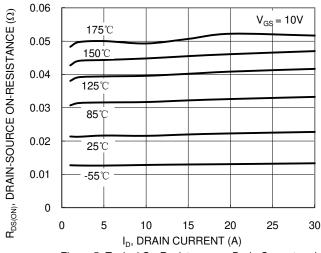
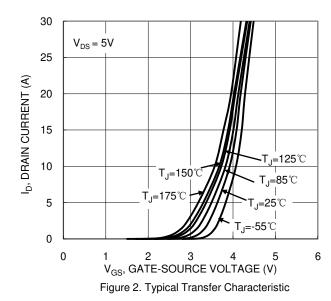


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



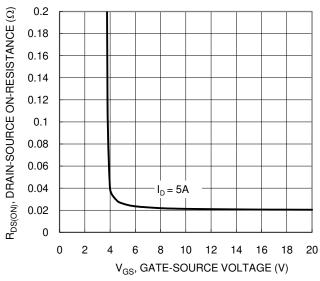


Figure 4. Typical Transfer Characteristic

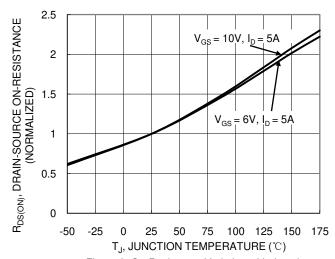


Figure 6. On-Resistance Variation with Junction Temperature



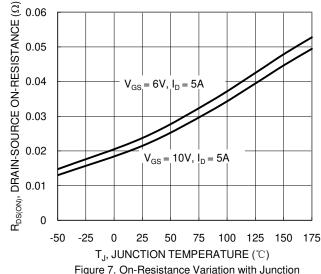
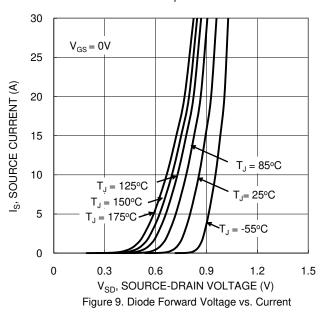
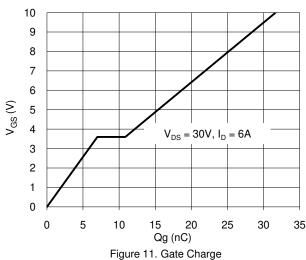


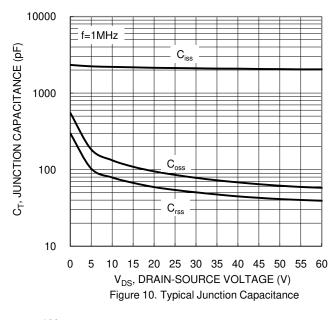
Figure 7. On-Resistance Variation with Junction Temperature

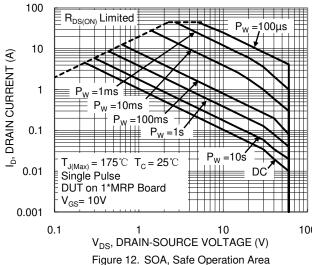




 $V_{GS(TH)},$ GATE THRESHOLD VOLTAGE (V) 3.5 3 $I_D = 1mA$ 2.5 $I_{D} = 250 \mu A$ 2 1.5 1 0.5 0 -50 -25 50 75 100 125 150 175 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







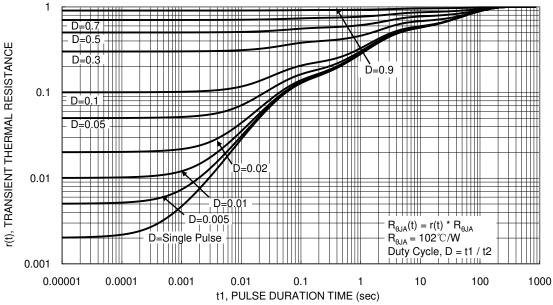


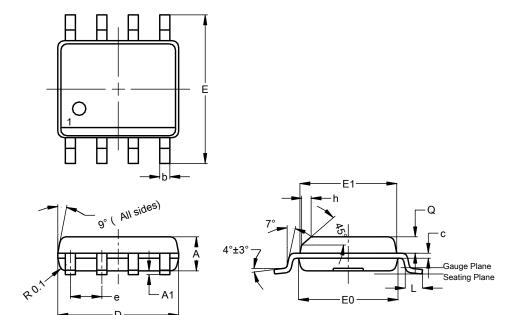
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

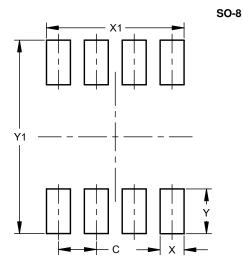
SO-8



SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Ε	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
Y1	6.50



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